

1-Line Bi-directional TVS Diode

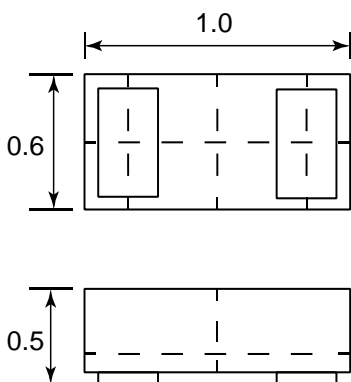
Description

The PESDU0521P1 is a bi-directional TVS diode, to provide fast-response time and low ESD clamping voltage, making this device an ideal solution for protecting voltage sensitive data and power line. The PESDU0521P1 complies with the IEC 61000-4-2 (ESD) standard with $\pm 30\text{kV}$ air and $\pm 30\text{kV}$ contact discharge. It is assembled into an ultra-small 1.0x0.6x0.5mm lead-free DFN package. The small size and high ESD protection make PESDU0521P1 an ideal choice to protect cellphone, digital cameras, audio players and many other portable applications.

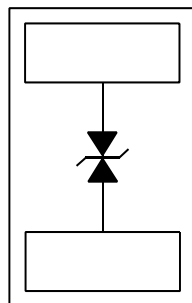
Features

- Ultra small package: 1.0x0.6mm
- Protects one data or power line
- Ultra low leakage: nA level
- Low operating voltage: 5V
- Low clamping voltage
- 2-pin leadless package
- Complies with following standards:
 - IEC 61000-4-2 (ESD) immunity test
 - Air discharge: $\pm 30\text{kV}$
 - Contact discharge: $\pm 30\text{kV}$
 - IEC61000-4-5 (Lightning) 8.5A (8/20 μs)
- RoHS Compliant

Dimensions and Pin Configuration



Package Dimensions



Circuit and Pin Schematic

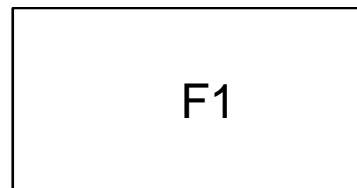
Mechanical Characteristics

- Package: DFN1006-2 (1.0x0.6mm)
- Lead Finish: NiPdAu
- Case Material: “Green” Molding Compound.
- Moisture Sensitivity: Level 3 per J-STD-020
- Marking Information: See Below

Applications

- Cellular Handsets and Accessories
- Personal Digital Assistants
- Notebooks and Handhelds
- Portable Instrumentation
- Digital Cameras
- Peripherals
- Audio Players
- Keypads, Side Keys, LCD Displays

Marking Information



F1 = Device Marking Code

Ordering Information

Part Number	Shipping	Reel Size
PESDU0521P1	10000/Tape & Reel	7 inch

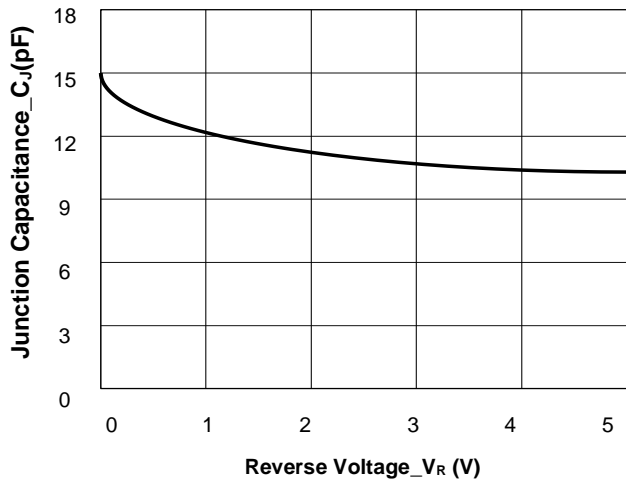
Absolute Maximum Ratings ($T_A=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Value	Unit
Peak Pulse Power (8/20 μs)	P_{PK}	110	W
Peak Pulse Current (8/20 μs)	I_{PP}	8.5	A
ESD per IEC 61000-4-2 (Air) ESD per IEC 61000-4-2 (Contact)	V_{ESD}	± 30 ± 30	kV
Operating Temperature Range	T_{OP}	-55 to +125	$^{\circ}\text{C}$
Storage Temperature Range	T_{STG}	-55 to +150	$^{\circ}\text{C}$

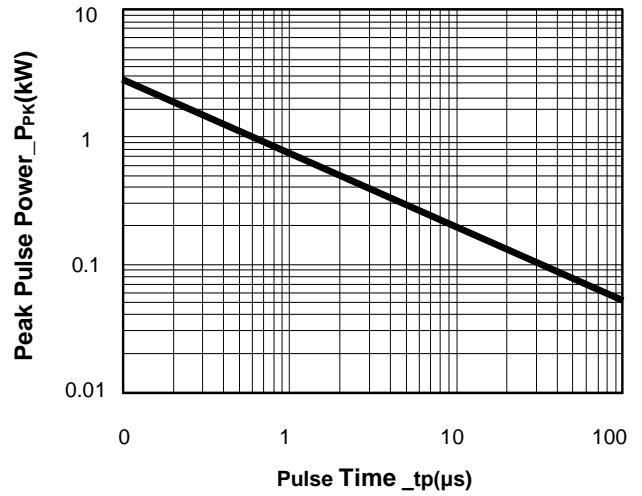
Electrical Characteristics ($T_A=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Min	Typ	Max	Unit	Test Condition
Reverse Working Voltage	V_{RWM}			5	V	
Breakdown Voltage	V_{BR}	5.6			V	$I_T = 1\text{mA}$
Reverse Leakage Current	I_R			0.1	μA	$V_{RWM} = 5\text{V}$
Clamping Voltage	V_C		7	9	V	$I_{PP} = 1\text{A}$ (8/20 μs pulse)
Clamping Voltage	V_C		10	13	V	$I_{PP} = 8.5\text{A}$ (8/20 μs pulse)
Junction Capacitance	C_J		15	18	pF	$V_R = 0.2\text{V}$, $f = 1\text{MHz}$

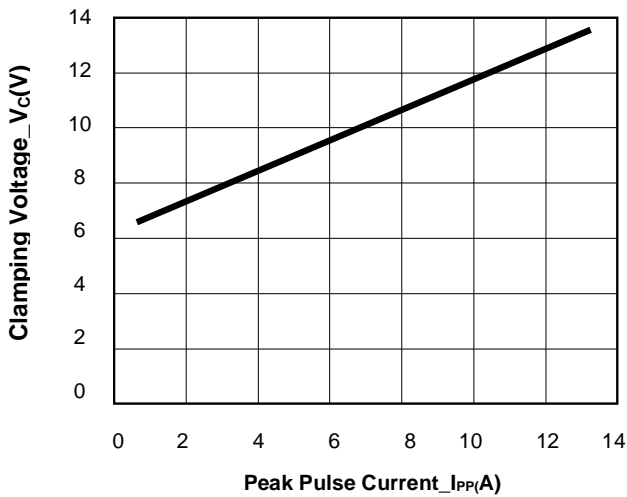
Typical Performance Characteristics (T_A=25°C unless otherwise Specified)



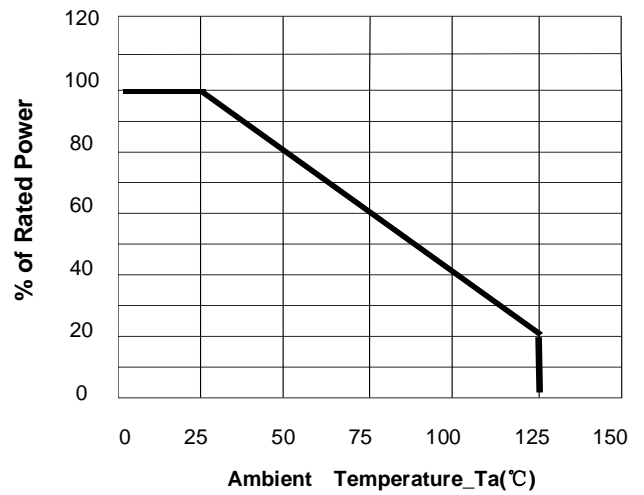
Junction Capacitance vs. Reverse Voltage



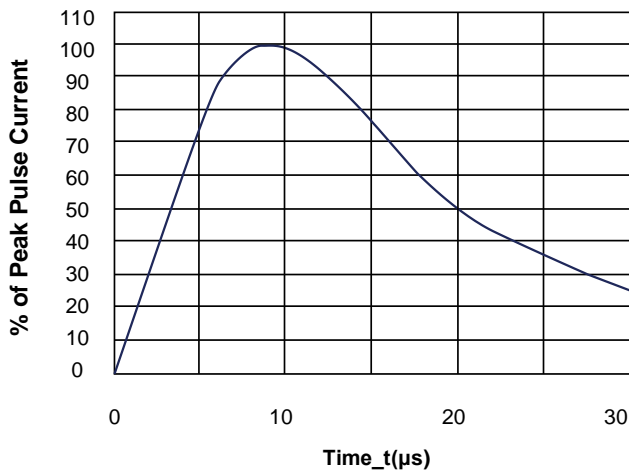
Peak Pulse Power vs. Pulse Time



Clamping Voltage vs. Peak Pulse Current

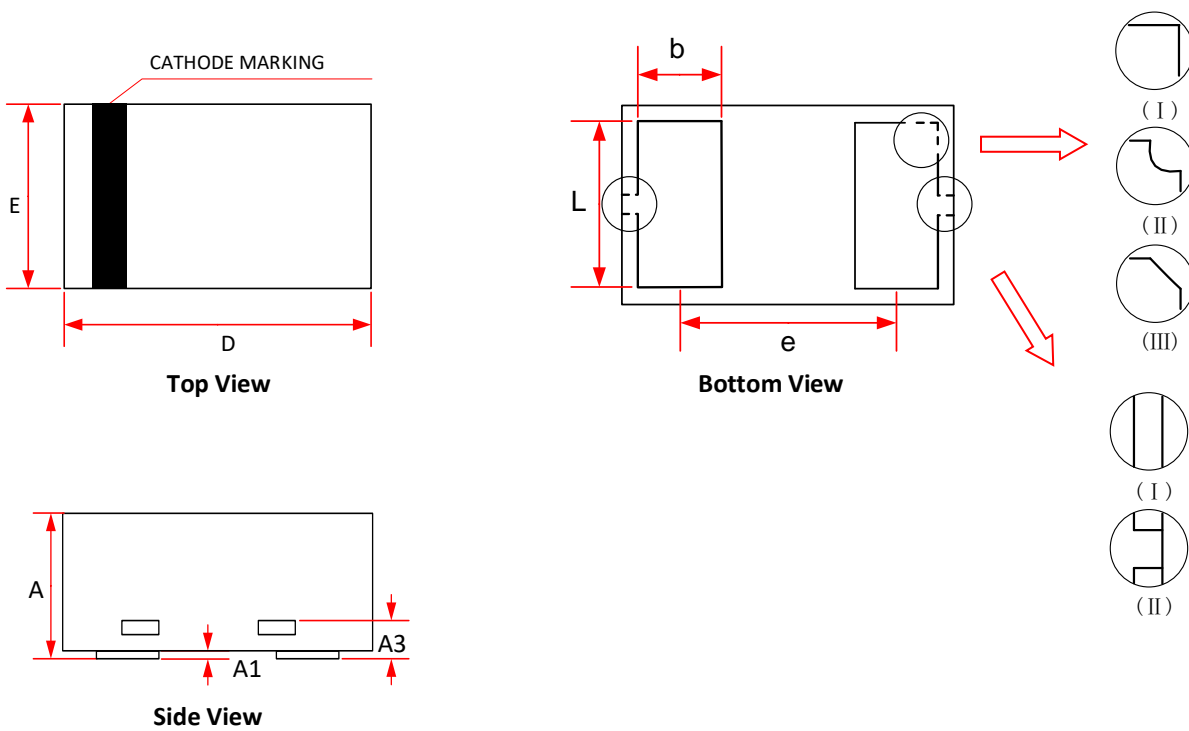


Power Derating Curve



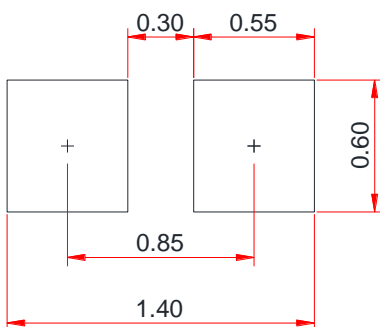
8/20μs Pulse Waveform

DFN1006-2 Package Outline Drawing



Symbol	Dimensions in Millimeters		
	Min.	Typ.	Max.
A	0.340	0.450	0.540
A1	0.000	0.020	0.050
A3	0.125 Ref.		
D	0.950	1.000	1.075
E	0.490	0.600	0.675
b	0.200	0.250	0.300
L	0.450	0.500	0.550
e	0.650 BSC		

Recommended PCB Layout (Unit: mm)



Notes:

This recommended land pattern is for reference purposes only. Please consult your manufacturing group to ensure your PCB design guidelines are met.

单击下面可查看定价，库存，交付和生命周期等信息

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